General Description

The GreenMOS® high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS® Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

Features

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

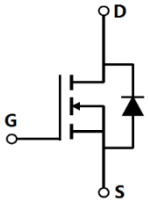
Key Performance Parameters

Parameter	Value	Unit
$V_{DS,\ min}$ @ $T_{j(max)}$	700	V
$I_{D,\ pulse}$	240	A
$R_{DS(ON)\ ,\ max}$ @ V_{GS}=10V	35	mΩ
Q_g	153.6	nC

Marking Information

Product Name	Package	Marking
OSG65R035HTF	TO247	OSG65R035HT

Package & Pin Information



Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	±30	V
Continuous drain current[1], T_C=25 °C	I_D	80	A
Continuous drain current[1], T_C=100 °C		50	
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	240	A
Continuous diode forward current[1], T_C=25 °C	I_S	80	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	240	A
Power dissipation[3] T_C=25 °C	P_D	455	W
Single pulsed avalanche energy[5]	E_{AS}	1700	mJ
MOSFET dv/dt ruggedness, V_{DS}=0…480 V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS}=0…480 V, I_{SD}≤I_D	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.27	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	V_{GS}=0 V, I_D=2 mA
		700				V_{GS}=0 V, I_D=2 mA, T_j=150 °C
Gate threshold voltage	$V_{GS(th)}$	2.8		4.0	V	V_{DS}=V_{GS}, I_D=2 mA
Drain-source on-state resistance	$R_{DS(ON)}$		0.028	0.035	Ω	V_{GS}=10 V, I_D=40 A
			0.075			V_{GS}=10 V, I_D=40 A, T_j=150 °C
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=30 V
				-100		V_{GS}=-30 V
Drain-source leakage current	I_{DSS}			5	μA	V_{DS}=650 V, V_{GS}=0 V
Gate resistance	R_G		2.4		Ω	f= 1 MHz, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		7549.2		pF	V_{GS}=0 V, V_{DS}=50 V, f=100 kHz
Output capacitance	C_{oss}		447.1		pF	
Reverse transfer capacitance	C_{rss}		13.2		pF	
Turn-on delay time	$t_{d(on)}$		52.3		ns	V_{GS}=10 V, V_{DS}=400 V, R_G=5 Ω, I_D=40 A
Rise time	t_r		86.8		ns	
Turn-off delay time	$t_{d(off)}$		165.2		ns	
Fall time	t_f		8.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		153.6		nC	V_{GS}=10 V, V_{DS}=400 V, I_D=40 A
Gate-source charge	Q_{gs}		41.8		nC	
Gate-drain charge	Q_{gd}		50.2		nC	
Gate plateau voltage	$V_{plateau}$		5.8		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	I_S=80 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		566.1		ns	V_R=400V, I_S=40 A, di/dt=100 A/μs
Reverse recovery charge	Q_{rr}		13.2		μC	
Peak reverse recovery current	I_{rrm}		45.9		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=100 V, V_{GS}=10 V, L=60 mH, starting T_j=25 °C.

Electrical Characteristics Diagrams

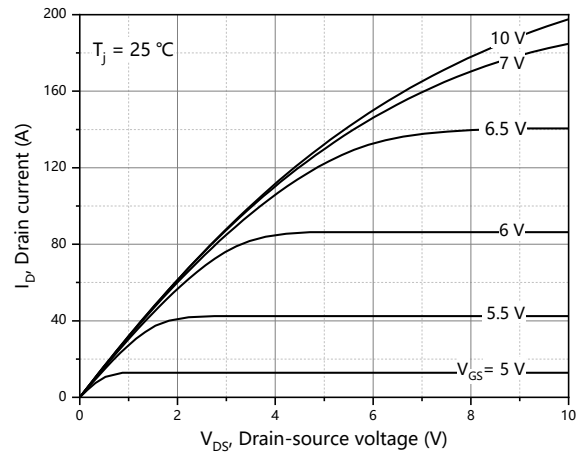


Figure 1. Typ. output characteristics

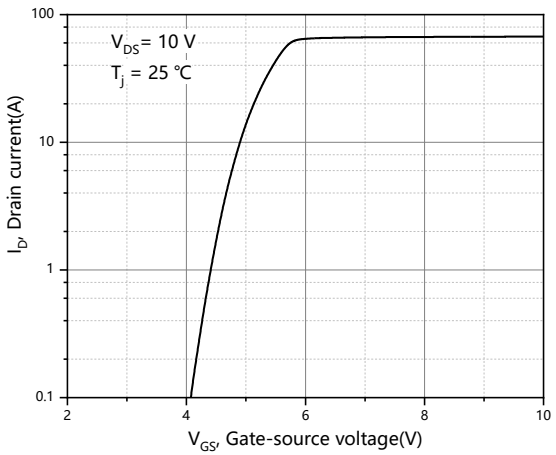


Figure 2. Typ. transfer characteristics

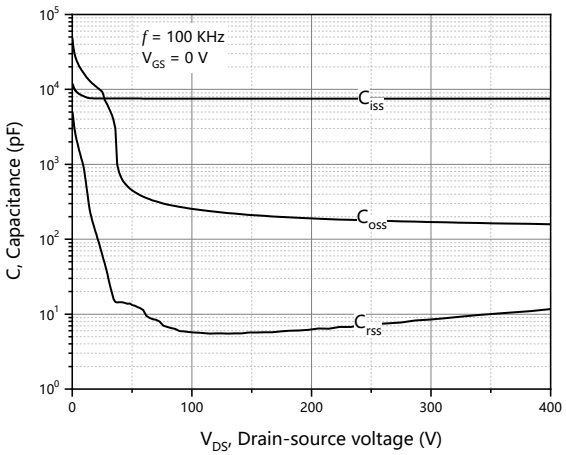


Figure 3. Typ. capacitances

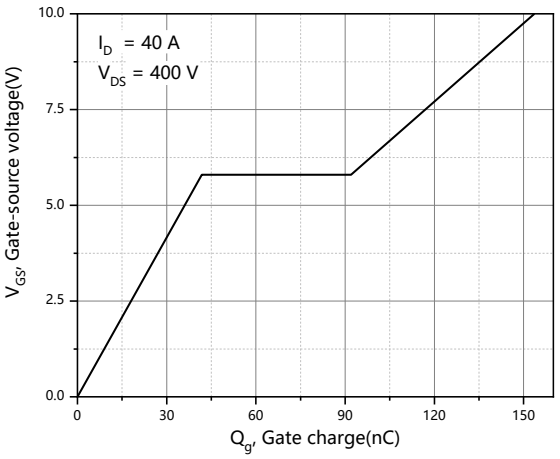


Figure 4. Typ. gate charge

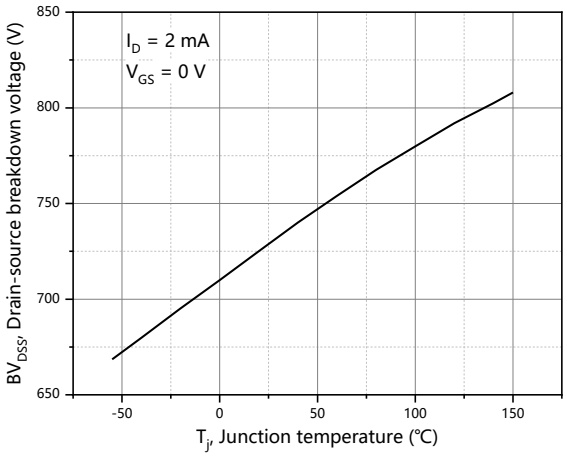


Figure 5. Drain-source breakdown voltage

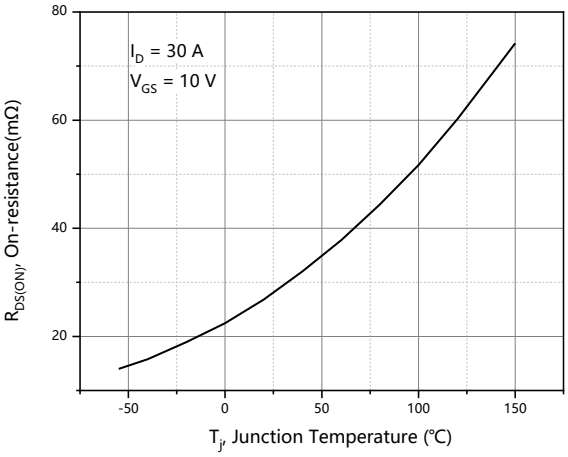


Figure 6. Drain-source on-state resistance

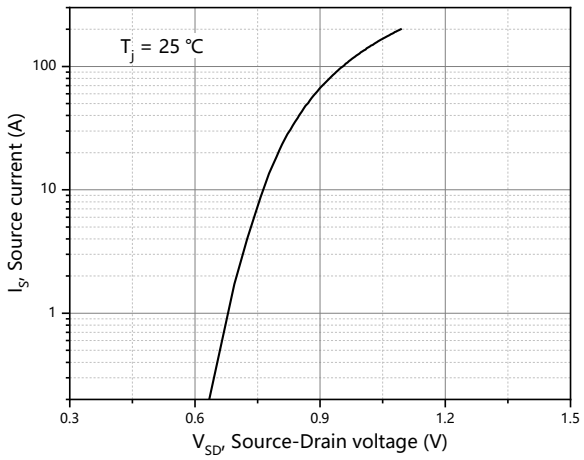


Figure 7. Forward characteristic of body diode

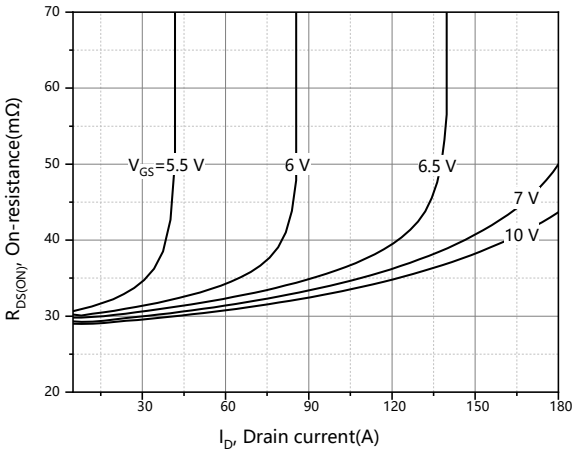


Figure 8. Drain-source on-state resistance

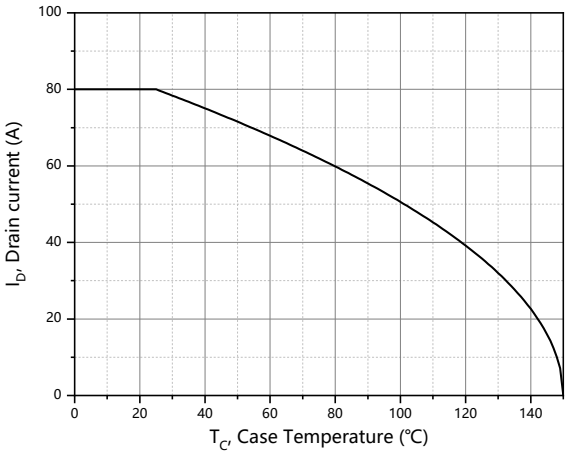


Figure 9. Drain current

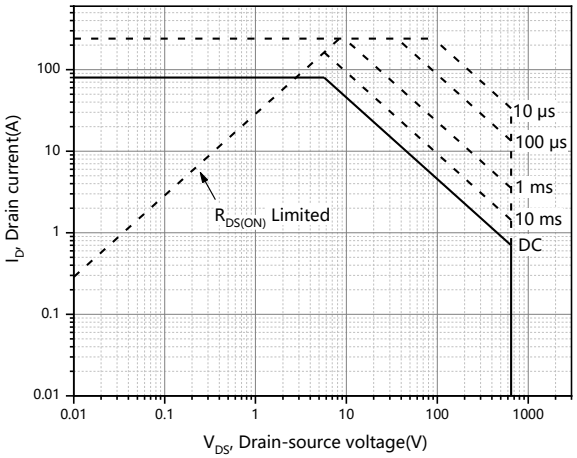


Figure 10. Safe operation area

Test circuits and waveforms

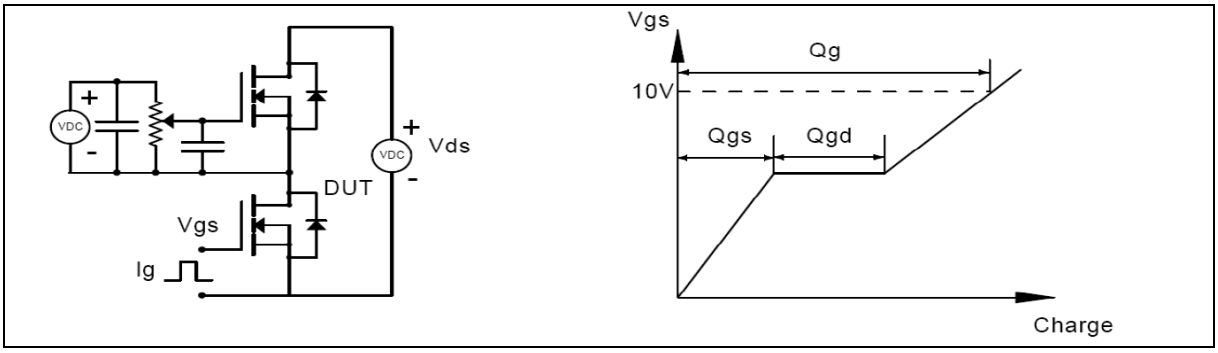


Figure 1. Gate charge test circuit & waveform

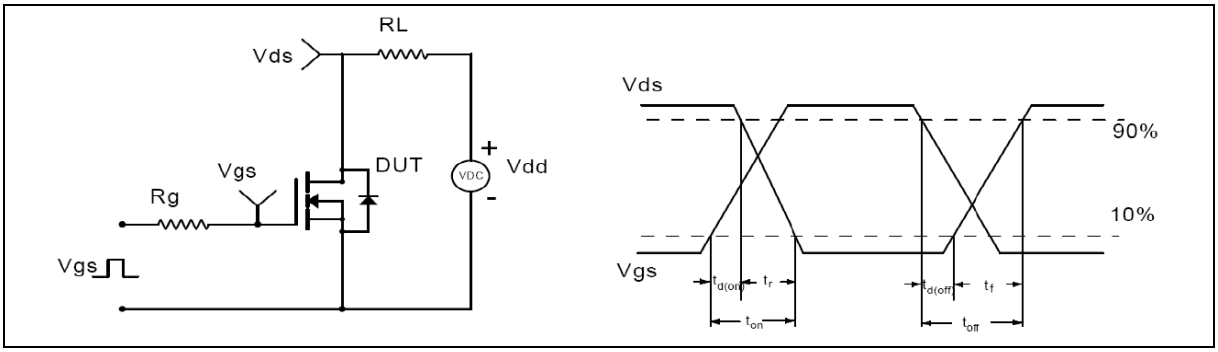


Figure 2. Switching time test circuit & waveforms

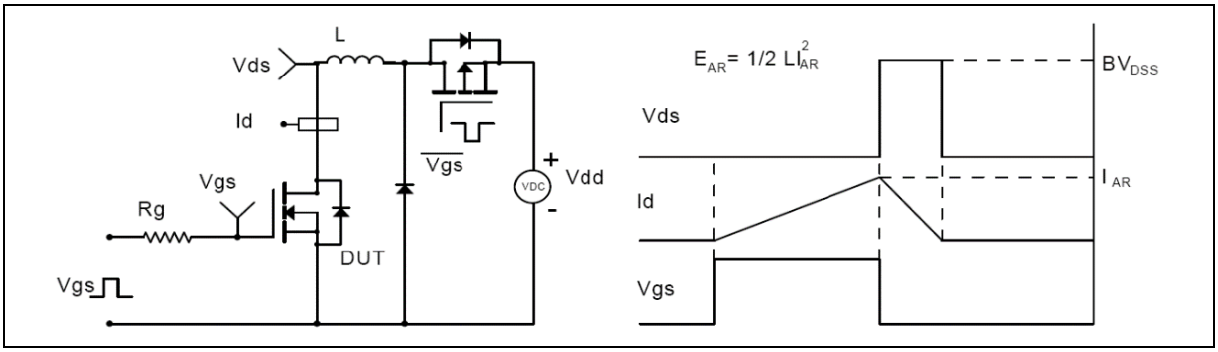


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

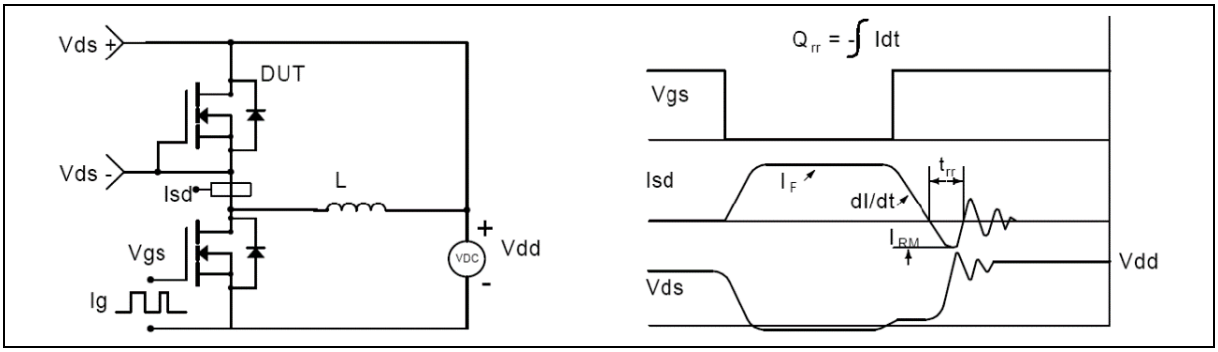
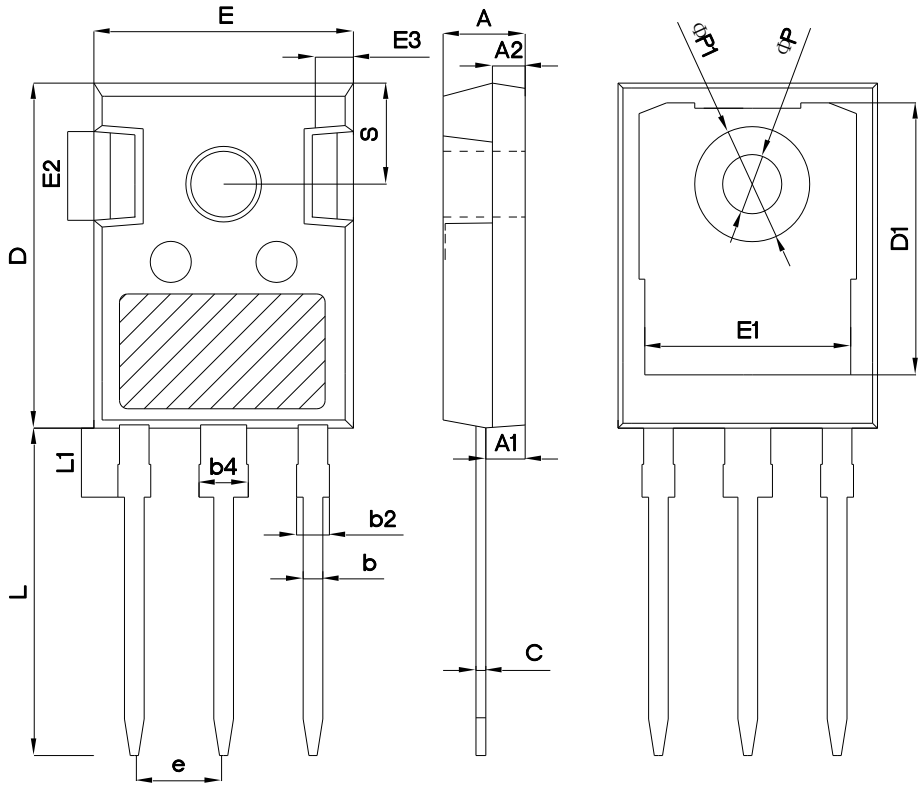


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44 BSC		
L	19.82	19.92	20.22
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.30
S	6.15 BSC		

Version1: TO247-C package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO247-C	30	11	330	6	1980

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R035HTF	TO247	yes	yes	yes

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